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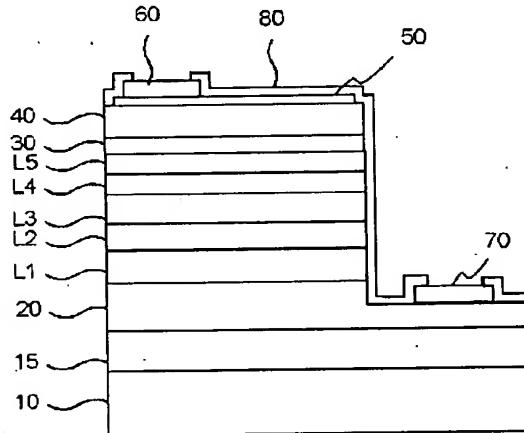
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(54) Title: III-NITRIDE COMPOUND SEMICONDUCTOR LIGHT EMITTING DEVICE



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(57) Abstract: The present invention provides a III-nitride compound semiconductor light emitting device comprising an active layer (30) which emits light and is interposed between a lower contact layer (20) made of n-GaN and an upper contact layer (40) made of p-GaN, in which a sequential stack of a lattice mismatch-reducing layer L3 made of $In_x Ga_{1-x} N$, an electron supply layer L4 made of n-GaN or n-Al_x Ga_{1-x} N and a crystal restoration layer L5 made of $In_x Ga_{1-x} N$ is interposed between the lower contact layer and the active layer, and further comprising an electron acceleration layer L1 made of n-GaN or undoped GaN and heterojunction electron barrier-removing layer L2, thereby the lattice mismatch between the lower contact layer (20) and the active layer (30) can be reduced.